MJE15028, MJE15030 (NPN), MJE15029, MJE15031 (PNP)

Complementary Silicon Plastic Power Transistors

These devices are designed for use as high-frequency drivers in audio amplifiers.

Features

- High Current Gain Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJE15028G, MJE15029G MJE15030G, MJE15031G	V _{CEO}	120 150	Vdc
Collector-Base Voltage MJE15028G, MJE15029G MJE15030G, MJE15031G	V _{CB}	120 150	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	I _C	8.0	Adc
Collector Current - Peak	I _{CM}	16	Adc
Base Current	I _B	2.0	Adc
Total Device Dissipation @ T _C = 25° C Derate above 25° C	P _D	50 0.40	W W/°C
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

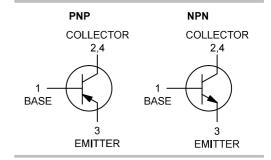
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W



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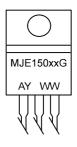
http://onsemi.com

8 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 120-150 VOLTS, 50 WATTS





MARKING DIAGRAM



MJE150xx = Device Code

x = 28, 29, 30, or 31

A = Assembly Location Y = Year

Y = Year

WW = Work Week

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.